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(54) **LIGHT-EMITTING DIODE CHIP AND
LIGHT-EMITTING DEVICE**

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(57) **ABSTRACT**

A light-emitting diode (LED) chip includes a semiconductor laminated layer including a first semiconductor layer, a light-emitting layer and a second semiconductor layer arranged from bottom to top, a transparent conductive layer disposed on the semiconductor laminated layer, a transparent bonding layer disposed on the transparent conductive layer, and a transparent substrate disposed on the transparent bonding layer. The second semiconductor layer includes a first sublayer and a second sublayer disposed on a part of an upper surface of the first sublayer, and a doping concentration of the first sublayer is lower than that of the second sublayer. The transparent conductive layer is in contact with an upper surface of the second sublayer and a part of the upper surface of the first sublayer around the second sublayer. The LED chip can improve the manufacturing yield and ensure the ohmic contact and uniform lateral current spreading.

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